

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	0	method manufacturing ternary nitride- based buffer layer light-emitting device comprising steps substrate introducing first reaction source group III element chamber temperature deposited	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2008/11/10 00:51

11/ 10/ 2008 12:51:46 AM

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